

### INCHANGE SEMICONDUCTOR

## **isc Silicon NPN Power Transistors**

# BU508DF

### DESCRIPTION

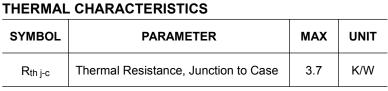
- · High Switching Speed
- High Voltage
- Built-in Integrated Diode
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

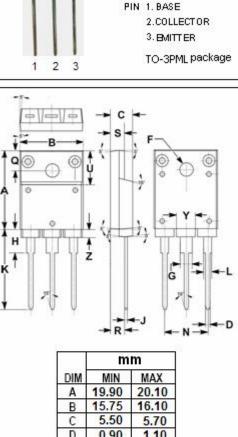
### **APPLICATIONS**

• Designed for use in horizontal deflection circuits of colour TV receivers.

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	1500	v	
V <sub>CEO</sub>	Collector-Emitter Voltage	700	V	
VEBO	BO Emitter-Base Voltage		V	
Ic	Ic Collector Current-Continuous		A	
I <sub>CM</sub>	I <sub>CM</sub> Collector Current-Peak		А	
IB	IB Base Current		А	
I <sub>BM</sub> Base Current-Peak		6	А	
Pc Collector Power Dissipation @Tc=25°C		34	W	
T <sub>J</sub> Junction Temperature		150	Ĉ	
Tstg	Storage Temperature	-65~150	°C	

## ABSOLUTE MAXIMUM RATINGS(Ta=25℃)





	U	0.90	1.10
-	F	3.30	3.50
	G	2.90	3.20
	Н	5.90	6.10
	J	0.595	0.70
1	K	21.10	22.50
1	L	1.90	2.25
	N	10.80	11.00
	0	4.90	5.10
	R	3.75	3.95
	S	3.20	3.60
1	U	9.90	10.10
- 3	Y	4.20	4.90

1.90 2.10

isc website: www.iscsemi.com

<sup>1</sup> *isc & iscsemi* is registered trademark

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### **ELECTRICAL CHARACTERISTICS**

#### $T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
Vceo(sus)	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 50mA ;I <sub>B</sub> = 0	700			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 4.5A; I <sub>B</sub> = 1.6A			1.0	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 4.5A ;I <sub>B</sub> = 2A			1.1	V
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> =0			300	mA
I <sub>CES</sub>	Collector Cutoff Current	V <sub>CB</sub> = BV <sub>CBO</sub> ;I <sub>E</sub> = 0 V <sub>CB</sub> = BV <sub>CBO</sub> ;I <sub>E</sub> = 0;T <sub>C</sub> =125°С	1		1.0 2.0	mA
hfe	DC Current Gain	Ic= 0.1A ; Vce= 5V	6	2	30	
fT	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.1A ; V <sub>CE</sub> = 5V		7	~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~	MHz
Сов	Output Capacitance	I <sub>E</sub> = 0 ; V <sub>CB</sub> = 10V;f <sub>test</sub> = 1MHz		125	and a second	pF
$V_{\text{ECF}}$	C-E Diode Forward Voltage	I <sub>F</sub> = 4.5A		1.6	2.0	V

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